

EAST - [10691300.wsp:1]

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DB: US-PGFLB; US-PAT; EPO; JPO ☐ Flush

Default operator: OR ☒ Highlight all hits immediately

4 and 2

☐ Drafts
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 L1: (77239) memory adj cell
 L2: (3284) MRAM
 L3: (48187) second adj2 transistor
 L4: (1996) 1 with 3
 L5: (52) 4 and 2
☐ Failed
☐ Saved
 S1: (4290) magnetic near random near access near memory or NRAM
 S2: (212) S1 and first near transistor
 S3: (827) S1 and stack
 S4: (43) S1 and stack and first near transistor
 S5: (0) S1 and 2T2MTJ
 S7: (0) S1 and nTnMTJ
 S6: (85) S1 and 1T1MTJ
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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 20050057986 A1	20050317	19	Magnetic spin based memory with inductive write lines	365/202	
2	<input type="checkbox"/>	<input type="checkbox"/>	US 20050024967 A1	20050203	15	Semiconductor memory device	365/207	
3	<input type="checkbox"/>	<input type="checkbox"/>	US 20040174728 A1	20040909	25	Semiconductor memory device	365/145	
4	<input type="checkbox"/>	<input type="checkbox"/>	US 20040160821 A1	20040819	19	HYBRID SEMICONDUCTOR - MAGNETIC SPIN BASED MEMORY	365/171	
5	<input type="checkbox"/>	<input type="checkbox"/>	US 20040160814 A1	20040819	19	HYBRID SEMICONDUCTOR - MAGNETIC SPIN BASED MEMORY WITH LOW TRANSMISSION BARRIER	365/158	
6	<input type="checkbox"/>	<input type="checkbox"/>	US 20040160800 A1	20040819	19	Stacked hybrid semiconductor-magnetic spin based memory	365/145	
7	<input type="checkbox"/>	<input type="checkbox"/>	US 20040160796 A1	20040819	20	METHOD OF MAKING HYBRID SEMICONDUCTOR - MAGNETIC SPIN BASED MEMORY	365/63	
8	<input type="checkbox"/>	<input type="checkbox"/>	US 20040141368 A1	20040722	33	Magnetoresistive random access memory device	365/158	
9	<input type="checkbox"/>	<input type="checkbox"/>	US 20040130939 A1	20040708	18	Nonvolatile semiconductor memory device	365/158	
10	<input type="checkbox"/>	<input type="checkbox"/>	US 20040125646 A1	20040701	14	MRAM architecture	365/158	
11	<input type="checkbox"/>	<input type="checkbox"/>	US 20040120200 A1	20040624	24	Current sense amplifier	365/210	365/206; 365/208

File Details HTML